

Product Overview

NTD4809N: Power MOSFET 30V 58A 9 mOhm Single N-Channel DPAK

For complete documentation, see the data sheet.

Power MOSFET 30 V, 58 A, Single N-Channel, DPAK/IPAK

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

Applications

- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

Part Electrical Specifications

Product	Compliance	Status	Chan- nel Polar- ity	Confi- gura- tion	$V_{SS}^{(BRD)}$ Min (V)	$V_{GS}^{(th)}$ Max (V)	$V_{GS}^{(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} =$ 2.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 4.5 V (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} =$ 10 V (mΩ)	Q_g Typ @ $V_{GS} =$ 4.5 V (nC)	Q_g Typ @ $V_{GS} =$ 10 V (nC)	C_{iss} Typ (pF)	Pack- age Type
NTD4809NT4G	Pb-free Halide free	Active	N- Chan- nel	Singl- e	30	20	2.5	58	2.63		14	9		25	1456	DPA K-3

For more information please contact your local sales support at www.onsemi.com.

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